Power Transistor (-50V, -3A) 2SB1308

Features

- 1) Low saturation voltage, typically VcE(sat) = -0.45V(Max.) at Ic / IB = -1.5A / -0.15A.
- 2) Excellent DC current gain characteristics.
- 3) Complements the 2SD1963.

●Packaging specifications and hre

Туре	2SB1308
Package	MPT3
hfE	PQR
Marking	BF*
Code	T100
Basic ordering unit (pieces)	1000

[★] Denotes hre

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	Vсво	-30	V
Collector-emitter voltage	Vceo	-20	V
Emitter-base voltage	VEBO	-6	V
Collector current	lc	-3	A (DC)
	l ic	-5	A (Pulse) *1
Collector power dissipation	Pc	0.5	
	FC	2.0	W *2
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55~+150	°C

^{*1} Single pulse, Pw=100ms

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	-30			V	Ic=-50 μ A	
Collector-emitter breakdown voltage	BVceo	-20	_	_	V	Ic=1mA	
Emitter-base breakdown voltage	ВУево	-6	_		V	I _E =-50 μ A	
Collector cutoff current	Ісво	_	_	-0.5	μΑ	V _{CB} =-20V	
Emitter cutoff current	IEBO	_	_	-0.5	μA	V _{EB} =-5V	
DC current transfer ratio	hre	82	_	390	_	Vce/lc=-2V/-0.5A	*
Collector-emitter saturation voltage	VCE(sat)	_	_	-0.45	V	Ic/Is=-1.5A/-0.15A	*
Transition frequency	fτ	_	120	_	MHz	Vc=-6V, I=50mA, f=30MHz	
Output capacitance	Cob	_	60	_	pF	Vcs=-20V , IE=0A , f=1MHz	

^{*} Measured using pulse current

(94S-166-B204)

Power Transistor (50V, 3A) 2SD1963

Features

- 1) Low saturation voltage, typically VcE(sat) = -0.45V (Max.) at lc / lb=-1.5A / -0.15A.
- 2) Excellent DC current gain characteristics.
- 3) Complements the 2SB1308.

●Packaging specifications and hre

Туре	2SD1963
Package	MPT3
hre	QRS
Marking	DG*
Code	T100
Basic ordering unit (pieces)	1000
* Denotes hre	

^{1.} DOI 10.00 111 L

●Absolute maximum ratings (Ta=25℃)

				_
Parameter	Symbol	Limits	Unit	
Collector-base voltage	VcBo	50	V	
Collector-emitter voltage	VCEO	20	V	
Emitter-base voltage	VEBO	6	V	
Collector current	lc	3	A (DC)	
	IC IC	5	A (Pulse)	*
Collector power dissipation	Pc	0.5	W	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55~+150	°C	

^{*} Single pulse, Pw=100ms

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	50			V	Ic=50 μ A	
Collector-emitter breakdown voltage	BVceo	20	_		V	Ic=1mA	
Emitter-base breakdown voltage	BVEBO	6	_	_	V	IE=50 μ A	
Collector cutoff current	Ісво	_	_	0.5	μΑ	VcB=40V	
Emitter cutoff current	Ієво	_	_	0.5	μΑ	VEB=5V	
DC current transfer ratio	hre	120	_	560	_	Vce/lc=2V/0.5A	*
Collector-emitter saturation voltage	VCE(sat)	_	0.25	0.45	V	Ic/Is=1.5A/0.15A	*
Transition frequency	fτ	_	150	_	MHz	VcE=6V , IE=-50mA , f=100MHz	
Output capacitance	Cob	_	35	_	рF	VcB=20V, IE=0A, f=1MHz	

[★] Measured using pulse current

(94S-342-D204)

^{*2} When mounted on a 40×40×0.7 ceramic board.

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